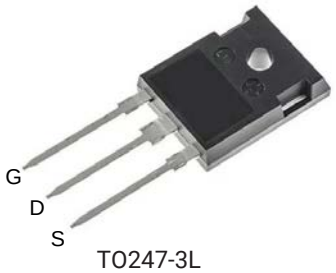
HC3M0075120D

SiC Power MOSFET N-Channel Enhancement Mode

Features

- C3M™ SiC MOSFET technology
- High blocking voltage with low On-resistance
- High speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Qrr)
- Halogen free, RoHS compliant



TO247-3L

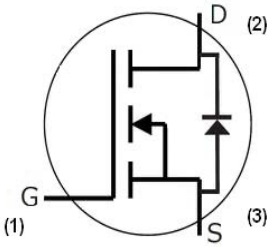
Package

Benefits

- Higher system efficiency
- Reduced cooling requirements
- Increased power density
- Increased system switching frequency

Applications

- Renewable energy
- EV battery chargers
- High voltage DC/DC converters
- Switch Mode Power Supplies



Ordering Part Number	Package	Marking	T_J , T_{stg} Range
HC3M0075120D	TO 247-3L	HC3M0075120D	-55 - 150 ˚C
HC3M0075120D-A	TO 247-3L	HC3M0075120D-A	-40 - 175 ˚C

Maximum Ratings (T_C = 25 ˚C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V	V_{GS} = 0 V, I_D = 100 µA	
V_{GSmax}	Gate - Source Voltage (dynamic)	-8/+19	V	AC (f >1 Hz)	Note: 1
V_{GSop}	Gate - Source Voltage (static)	-4/+15	V	Static	Note: 2
I_D	Continuous Drain Current	32	A	V_{GS} = 15 V, T_C = 25˚C	Fig. 19
		23		V_{GS} = 15 V, T_C = 100˚C	
$I_{D(pulse)}$	Pulsed Drain Current	80	A	Pulse width t_P limited by T_{jmax}	Fig. 22
P_D	Power Dissipation	136	W	T_C=25˚C, T_J = 175 ˚C	Fig. 20
T_J , T_{stg}	Operating Junction and Storage Temperature	-40 to +175	˚C		
T_L	Solder Temperature	260	˚C	1.6mm (0.063”) from case for 10s	
M_d	Mounting Torque	1 8.8	Nm lbf-in	M3 or 6-32 screw	

Note (1): When using MOSFET Body Diode V_{GSmax} = -4V/+19V
Note (2): MOSFET can also safely operate at 0/+15 V

Electrical Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	V_{GS} = 0 V, I_D = 100 µA	
$V_{GS(th)}$	Gate Threshold Voltage	1.8	2.5	3.6	V	V_{DS} = V_{GS}, I_D = 5 mA	Fig. 11
			2.2		V	V_{DS} = V_{GS}, I_D = 5 mA, T_J = 175ºC	
I_{DSS}	Zero Gate Voltage Drain Current		1	100	µA	V_{DS} = 1200 V, V_{GS} = 0 V	
I_{GSS}	Gate-Source Leakage Current		10	250	nA	V_{GS} = 15 V, V_{DS} = 0 V	
$R_{DS(on)}$	Drain-Source On-State Resistance		75	90	mΩ	V_{GS} = 15 V, I_D = 20 A	Fig. 4, 5, 6
			120			V_{GS} = 15 V, I_D = 20A, T_J = 175ºC	
g_{fs}	Transconductance		12		S	V_{DS}= 20 V, I_{DS}= 20 A	Fig. 7
			13			V_{DS}= 20 V, I_{DS}= 20 A, T_J = 175ºC	
C_{iss}	Input Capacitance		1390		pF	V_{GS} = 0 V, V_{DS} = 1000 V f = 1 MHz V_{AC} = 25 mV	Fig. 17, 18
C_{oss}	Output Capacitance		58				
C_{rss}	Reverse Transfer Capacitance		2				
E_{oss}	C_{oss} Stored Energy		33		µJ		Fig. 16
E_{ON}	Turn-On Switching Energy (SiC Diode FWD)		564		µJ	V_{DS} = 800 V, V_{GS} = -4 V/15 V, I_D = 20A, $R_{G(ext)}$ = 0Ω, L= 157 µH, T_J = 150ºC	Fig. 26, 29
E_{OFF}	Turn Off Switching Energy (SiC Diode FWD)		186				
E_{ON}	Turn-On Switching Energy (Body Diode FWD)		924		µJ	V_{DS} = 800 V, V_{GS} = -4 V/15 V, I_D = 20A, $R_{G(ext)}$ = 0Ω, L= 157 µH, T_J = 150ºC	Fig. 26, 29
E_{OFF}	Turn Off Switching Energy (Body Diode FWD)		162				
$t_{d(on)}$	Turn-On Delay Time		56		ns	V_{DD} = 800 V, V_{GS} = -4 V/15 V I_D = 20 A, $R_{G(ext)}$ = 0 Ω, Timing relative to V_{DS} Inductive load	Fig. 27, 28
t_r	Rise Time		17				
$t_{d(off)}$	Turn-Off Delay Time		32				
t_f	Fall Time		13				
$R_{G(int)}$	Internal Gate Resistance		9.0		Ω	f = 1 MHz, V_{AC} = 25 mV	
Q_{gs}	Gate to Source Charge		17		nC	V_{DS} = 800 V, V_{GS} = -4 V/15 V I_D = 20 A Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		20				
Q_g	Total Gate Charge		54				

Reverse Diode Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	4.5		V	V_{GS} = -4 V, I_{SD} = 10 A	Fig. 8, 9, 10
		4.0		V	V_{GS} = -4 V, I_{SD} = 10 A, T_J = 175 °C	
I_S	Continuous Diode Forward Current		26	A	V_{GS} = -4 V, T_J = 25 ˚C	Note 1
$I_{S, pulse}$	Diode pulse Current	80		A	V_{GS} = -4 V, pulse width t_P limited by T_{jmax}	Note 1
t_{rr}	Reverse Recover time	48		ns	V_{GS} = -4 V, I_{SD} = 20 A, V_R = 800 V dif/dt = 2800 A/µs, T_J = 150 °C	Note 1
Q_{rr}	Reverse Recovery Charge	279		nC		
I_{rrm}	Peak Reverse Recovery Current	9		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.97	1.1	°C/W		Fig. 21
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient		40			

Typical Performance

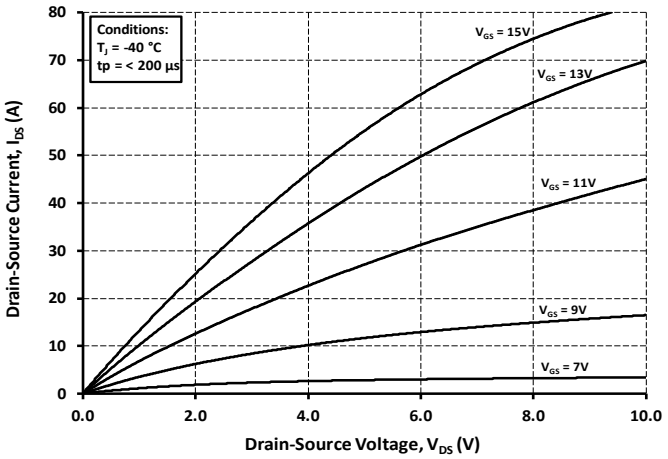


Figure 1. Output Characteristics T_J = -40 ºC

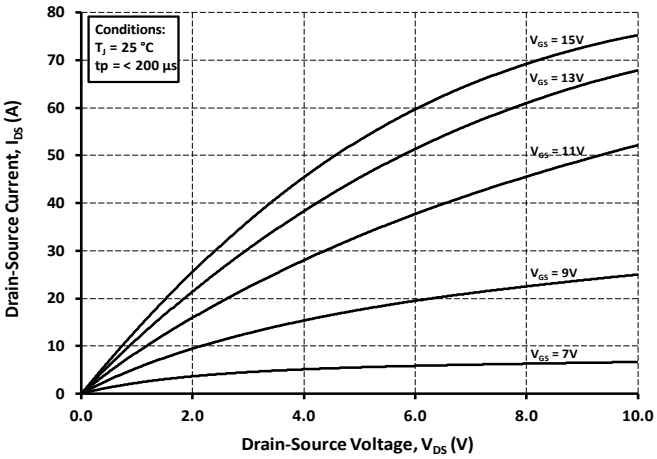


Figure 2. Output Characteristics T_J = 25 ºC

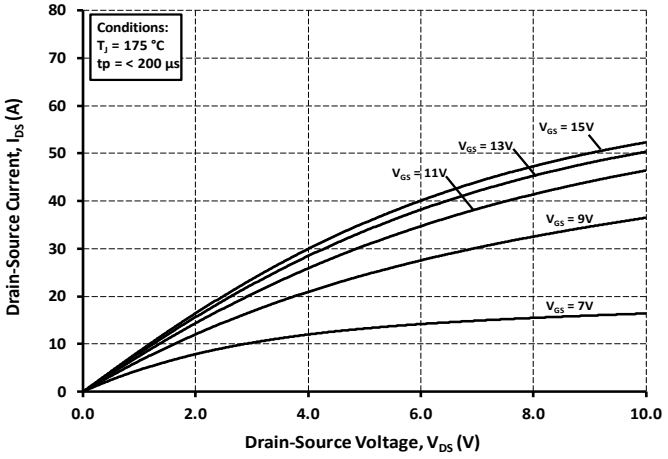


Figure 3. Output Characteristics T_J = 175 ºC

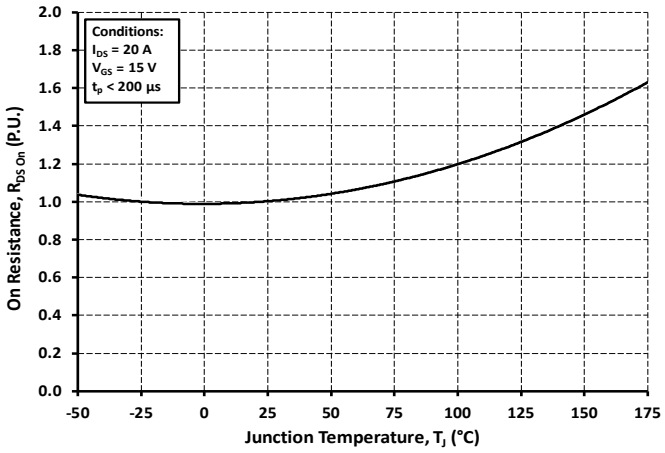


Figure 4. Normalized On-Resistance vs. Temperature

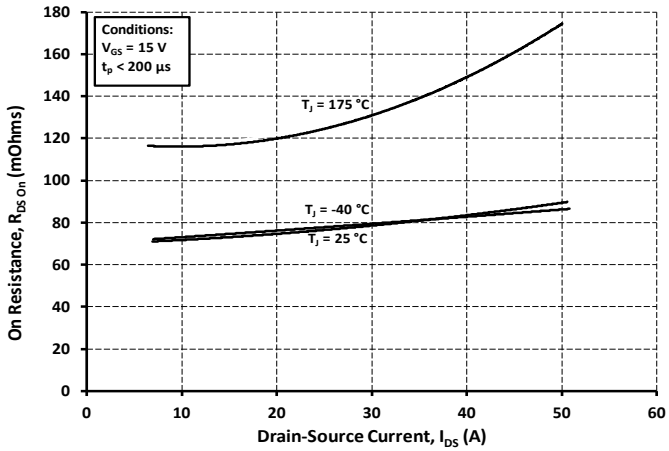


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

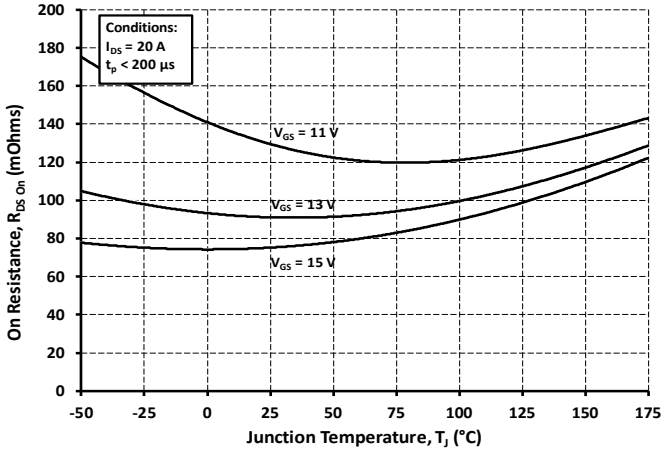


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

Typical Performance

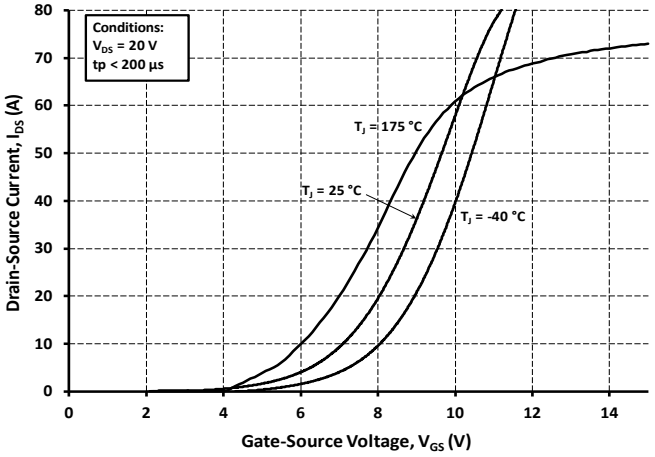


Figure 7. Transfer Characteristic for Various Junction Temperatures

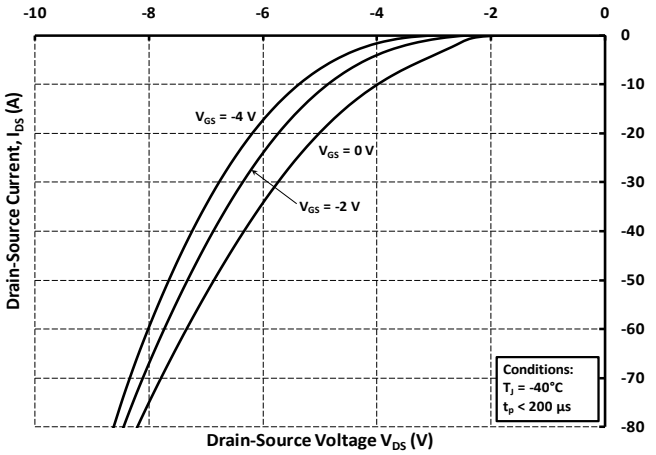


Figure 8. Body Diode Characteristic at -40 ºC

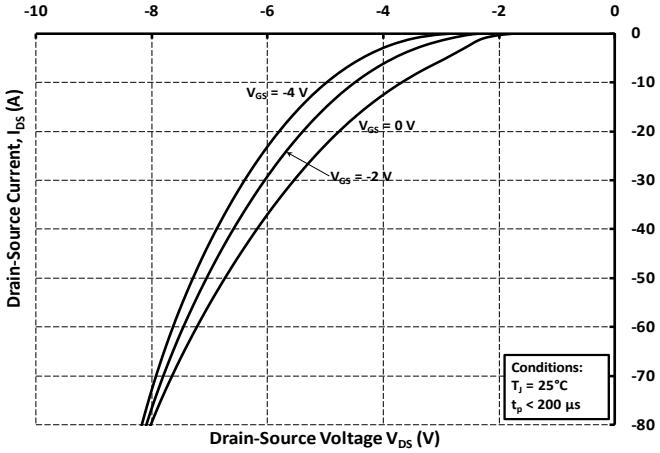


Figure 9. Body Diode Characteristic at 25 ºC

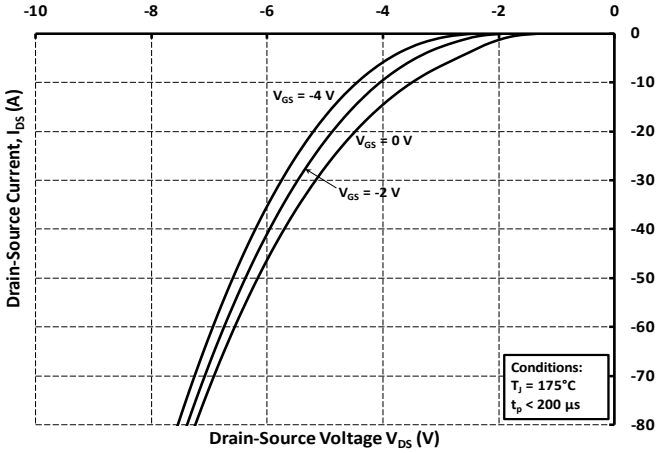


Figure 10. Body Diode Characteristic at 175 ºC

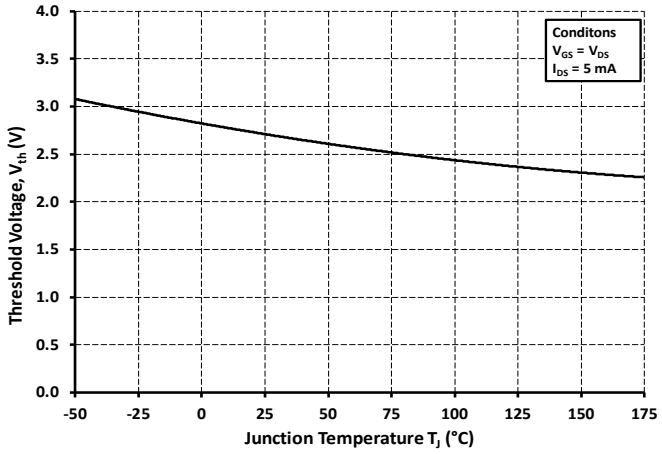


Figure 11. Threshold Voltage vs. Temperature

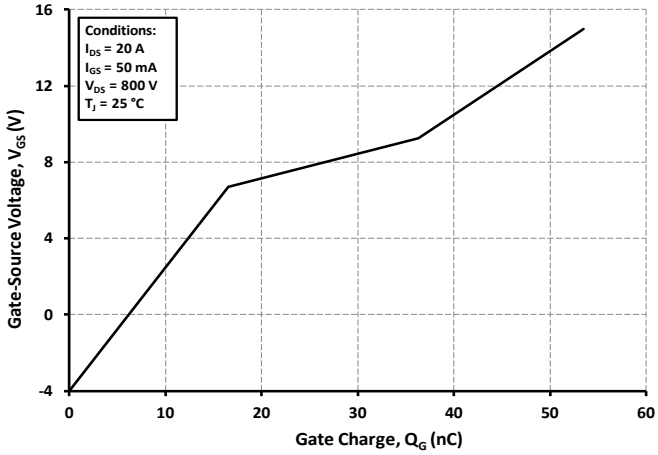


Figure 12. Gate Charge Characteristics

Typical Performance

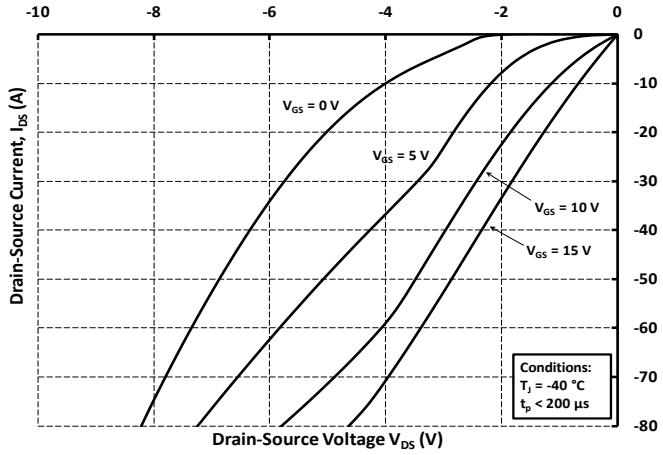


Figure 13. 3rd Quadrant Characteristic at -40 ºC

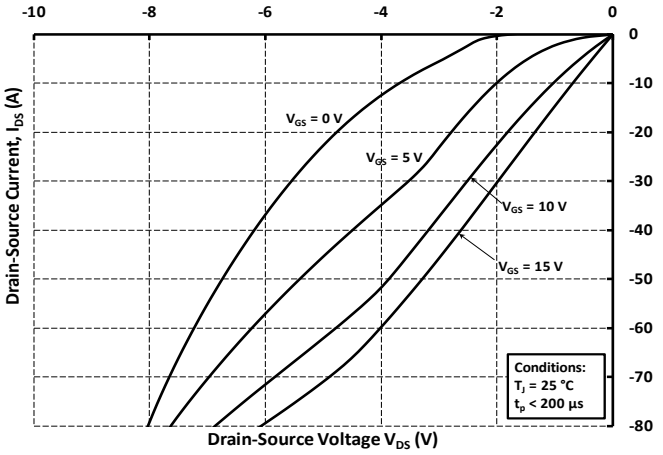


Figure 14. 3rd Quadrant Characteristic at 25 ºC

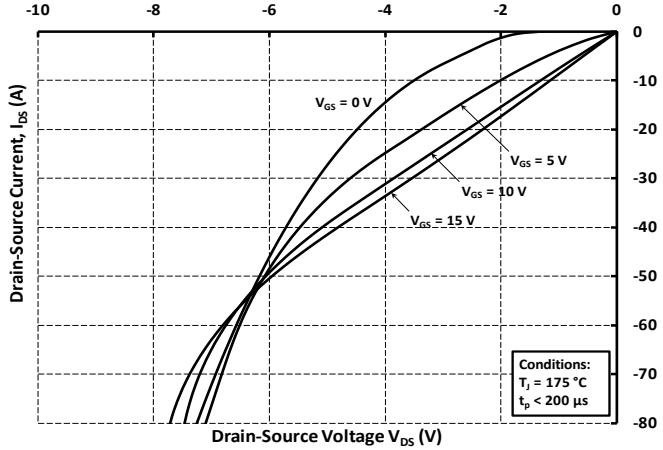


Figure 15. 3rd Quadrant Characteristic at 175 ºC

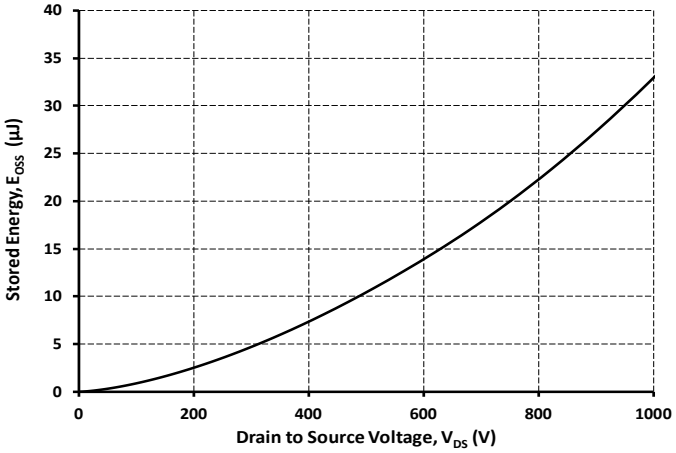


Figure 16. Output Capacitor Stored Energy

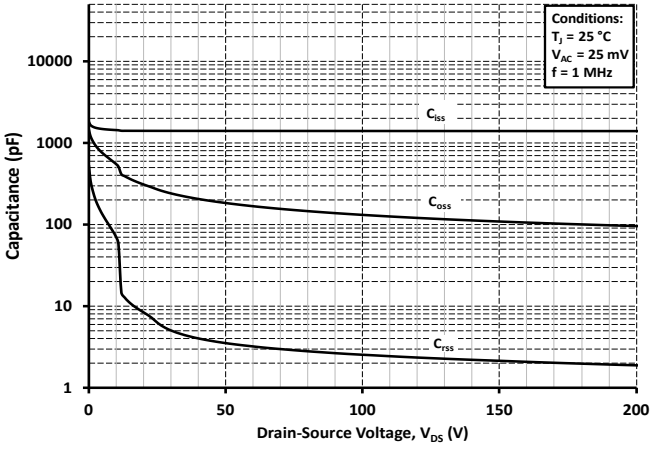


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

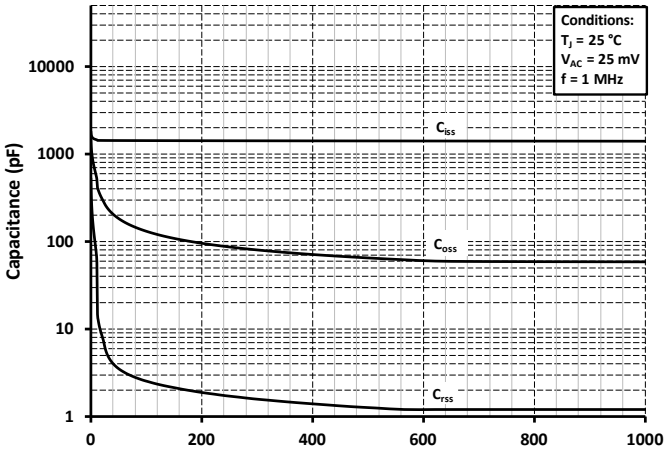


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1000V)

Typical Performance

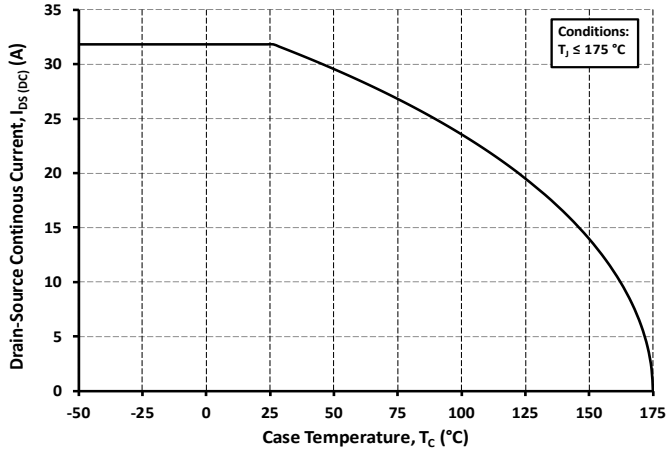


Figure 19. Continuous Drain Current Derating vs. Case Temperature

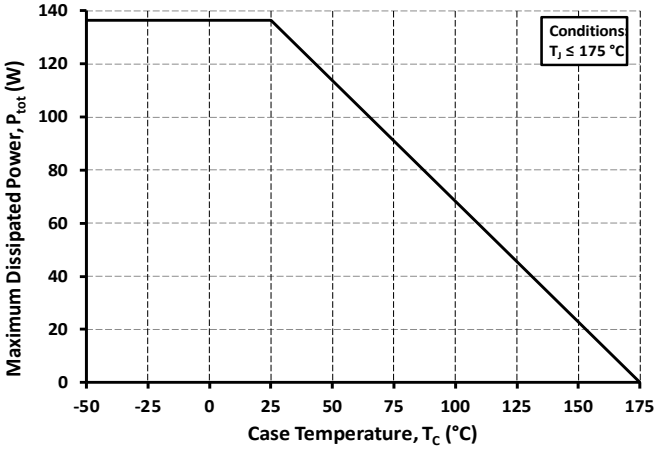


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

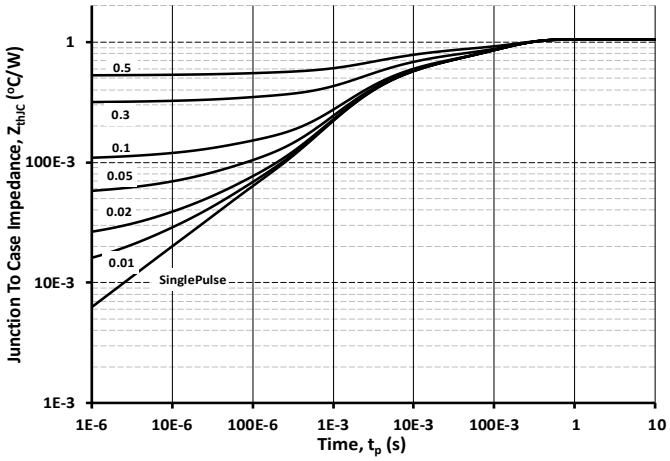


Figure 21. Transient Thermal Impedance (Junction - Case)

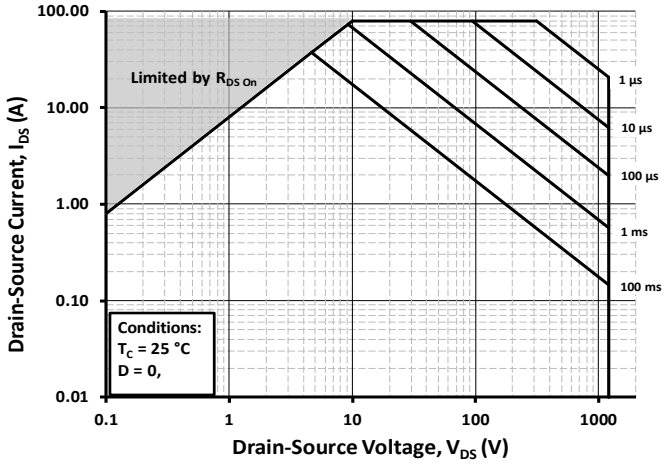


Figure 22. Safe Operating Area

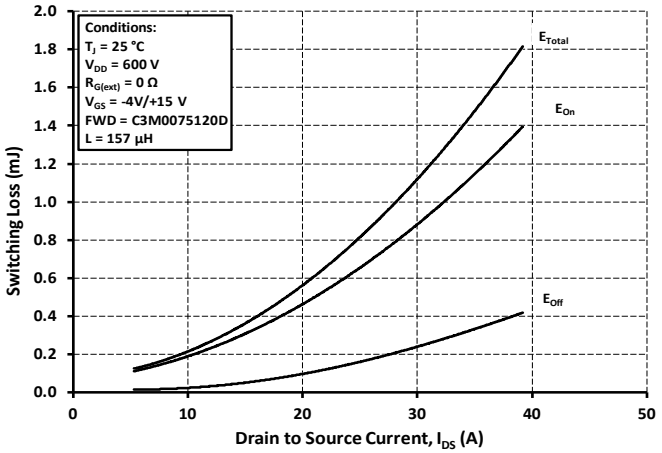


Figure 23. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 600V)

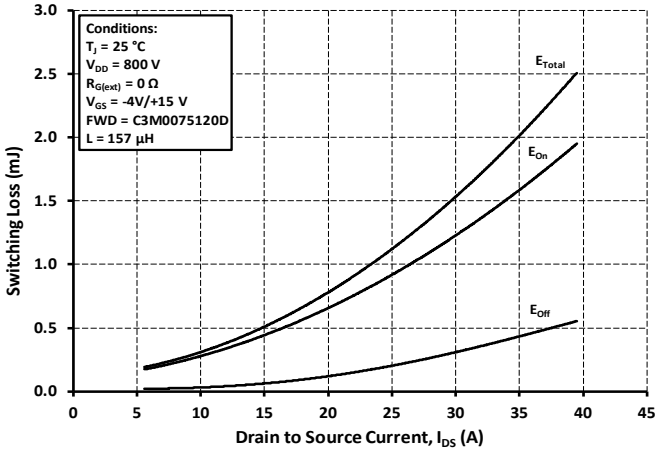


Figure 24. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 800V)

Typical Performance

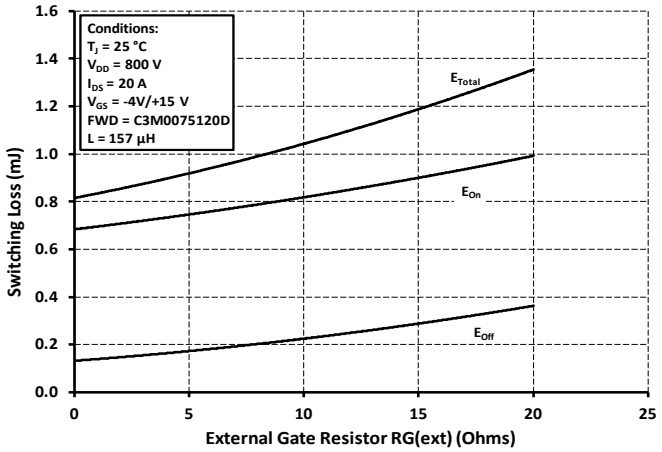


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

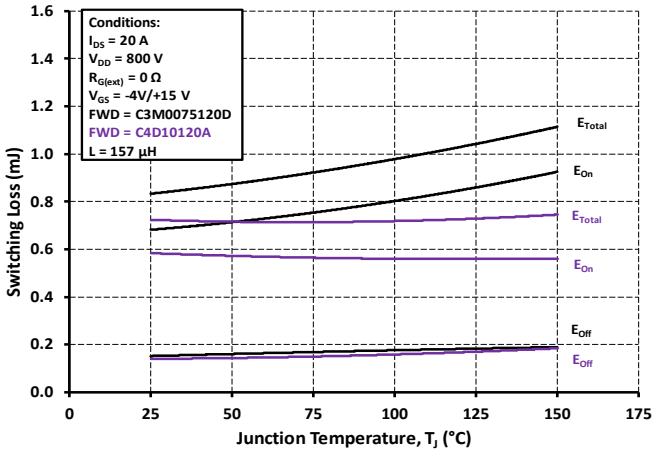


Figure 26. Clamped Inductive Switching Energy vs. Temperature

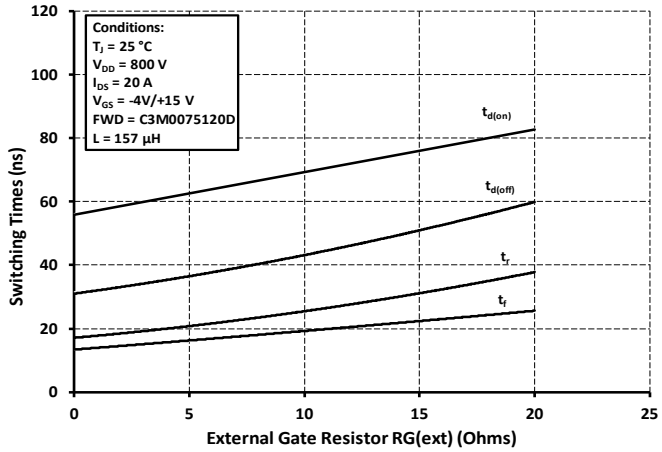


Figure 27. Switching Times vs. $R_{G(ext)}$

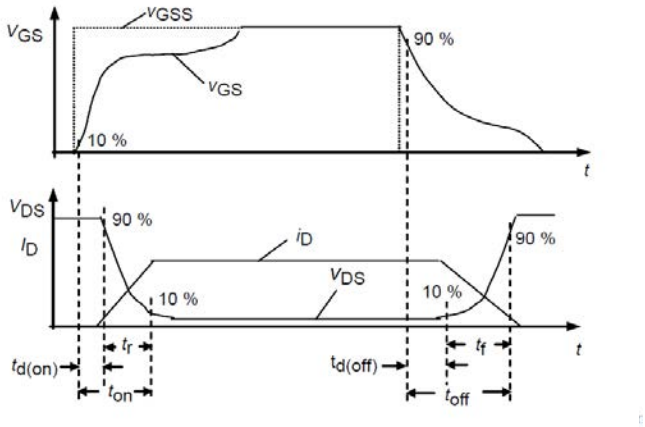


Figure 28. Switching Times Definition

Test Circuit Schematic

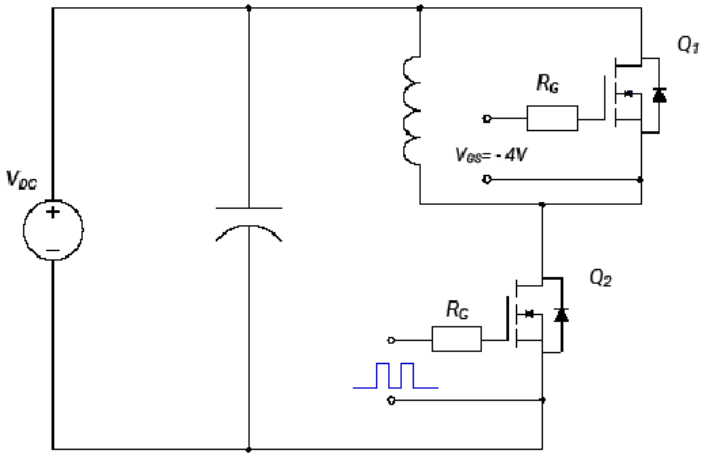
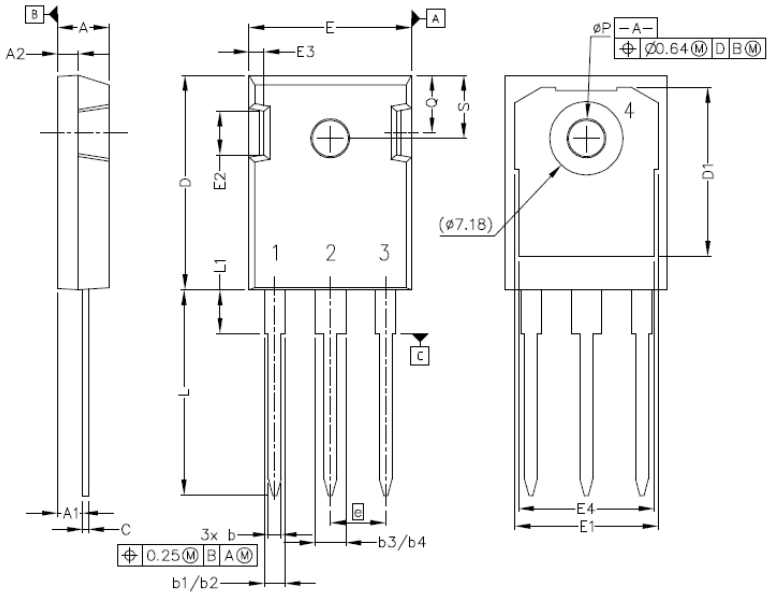


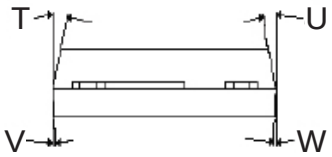
Figure 29. Clamped Inductive Switching
Waveform Test Circuit

Note (3): Turn-off and Turn-on switching energy and timing values measured using SiC MOSFET Body Diode as shown above.

Package Dimensions

Package TO247-3L



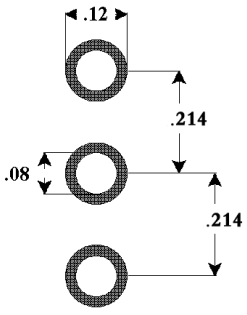


Pinout Information:

- Pin 1 = Gate
- Pin 2, 4 = Drain
- Pin 3 = Source

POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.042	.052	1.07	1.33
b1	.075	.095	1.91	2.41
b2	.075	.085	1.91	2.16
b3	.113	.133	2.87	3.38
b4	.113	.123	2.87	3.13
c	.022	.027	0.55	0.68
D	.819	.831	20.80	21.10
D1	.640	.695	16.25	17.65
D2	.037	.049	0.95	1.25
E	.620	.635	15.75	16.13
E1	.516	.557	13.10	14.15
E2	.145	.201	3.68	5.10
E3	.039	.075	1.00	1.90
E4	.487	.529	12.38	13.43
e	.214 BSC		5.44 BSC	
N	3		3	
L	.780	.800	19.81	20.32
L1	.161	.173	4.10	4.40
ØP	.138	.144	3.51	3.65
Q	.216	.236	5.49	6.00
S	.238	.248	6.04	6.30
T	9°	11°	9°	11°
U	9°	11°	9°	11°
V	2°	8°	2°	8°
W	2°	8°	2°	8°

Recommended Solder Pad Layout



TO247-3L

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